

PATENT CLAIMS

1. Composition for the production of semiconductors, comprising
H₂SiF₆ and/or HBF₄ in a total amount of 10 – 500 mg/kg, 12 – 17%
5 by weight of H₂SO₄, 2 – 4% by weight of H₂O₂, optionally in combination with additives, in aqueous solution.
2. Use of a composition comprising H₂SiF₆ and/or HBF₄ as residual
polymer remover in a process step in the production of semiconductors.
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3. Use according to Claim 2 for the removal of residual polymers from
Al or Al-containing conductor tracks.
4. Use according to Claim 2 for the removal of residual polymers after
dry etching on metal conductor tracks and contact holes.
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5. Use of a composition according to Claim 1 for the removal of residual
polymers from aluminium or copper/aluminium alloys.
6. Use of a composition comprising H₂SiF₆ and/or HBF₄ in a total
20 amount of 10 – 500 mg/kg, 12 – 17% by weight of H₂SO₄, 2 – 4% by weight of H₂O₂, optionally in combination with additives, in aqueous solution, according to one or more of Claims 2 – 5.
7. Use according to one or more of Claims 2 – 6 for the removal of
25 residual polymers in a process step in the production of semiconductors using a spin etcher or in a tank unit.
8. Process for the removal of residual polymers from Al or Al-containing
conductor tracks, characterised in that residual polymers are
30 removed using a composition according to Claim 1.